



Integrated Device Technology, Inc.
6024 Silver Creek Valley Road, San Jose, CA 95138

PRODUCT/PROCESS CHANGE NOTICE (PCN)

PCN #: **Q1703-01** DATE: **O ay 2, 2017**

Product Affected: F2915NBGK(8)

MEANS OF DISTINGUISHING CHANGED DEVICES:

- Product Mark
- Back Mark
- Date Code ZA marked on package topmark
- Other

Date Effective: **August 2, 2017**

Contact: IDT PCN DESK
E-mail: pcndesk@idt.com

Attachment: Yes No
Samples: Please contact your local sales representative for sample request.

DESCRIPTION AND PURPOSE OF CHANGE:

- Die Technology
- Wafer Fabrication Process This notification is to advise that IDT has made a minor design change to improve ESD performance for HBM from 1000V to 1500V. The datasheet has been updated.
- Assembly Process
- Equipment
- Material Characterization has confirmed the effectiveness of this change to meet the enhanced performance.
- Testing
- Manufacturing Site There is no change on the orderable part number.
- Data Sheet
- Other - Die revision The current version of this device will be discontinued as of the effective date on this notice.

RELIABILITY/QUALIFICATION SUMMARY:

There is no expected change to the product quality or reliability performance.

CUSTOMER ACKNOWLEDGMENT OF RECEIPT:

IDT records indicate that you require written notification of this change. Please use the acknowledgement below or E-Mail to grant approval or request additional information. If IDT does not receive acknowledgement within 30 days of this notice it will be assumed that this change is acceptable.
IDT reserves the right to ship either version manufactured after the process change effective date until the inventory on the earlier version has been depleted.

Customer: _____ **Approval for shipments prior to effective date.**
Name/Date: _____ E-Mail Address: _____
Title: _____ Phone # /Fax #: _____

CUSTOMER COMMENTS: _____

IDT ACKNOWLEDGMENT OF RECEIPT:

RECD. BY: _____ DATE: _____



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ATTACHMENT I - PCN #: Q1703-01

PCN Type: Die Revision Change

Data Sheet Change: Yes

Detail of Change:

This notification is to advise that IDT has made a minor design change to improve ESD performance for HBM from 1000V to 1500V. The datasheet has been updated.

The 1500V HBM rating of the new device is supported by Qualification.

There is no change on the orderable part number.

The current version of this device will be discontinued as of the effective date on this notice.

There is no change in die technology/process.

Samples are available for customer evaluation upon request.

Refer to the attachment for Qual Reports.

Product Qualification Report

Date: 2/24/2016

Product Type: IDTF2915 – High Reliability SP5T RF Switch			
Product Option	F2915	Process Technology:	CM018, CSOI7RF
Base Product	AN703	Fab Location:	GF – Altis (France)
Package Type:	VFQFP-N 24L	Assembly Location:	ASECL - Taiwan

Test Description	Conditions	Sample Size	Results (Rej/SS)	Comments
High Temperature Operating Life	JESD22-A108, 3.6V, Tj +150°C, 1000 hrs	77	0/77	Pass
ESD: Human Body Model	JESD22-A114 (JS-001) Classification	3	Classification	Class 1C (1500V)
ESD: Charged Device Model	JESD22-C101 Classification	3	Classification	Class C3 (1000V)
Latch-Up	JESD78	6	0/6	Pass. Ta at 105°C
Electrical Characterization	Datasheet	30	Results reported in Datasheet	Complete
Temperature Cycling [§]	JESD22-A104, -55°C to +125°C, 700 cycles	25	0/25	Pass
Highly Accelerated Temperature and Humidity stress (Biased) [§]	JESD22-A110, +130°C, 85% R.H., Vcc _{max} , 96 hrs	25	0/25	Pass
High Temperature Storage Life	JESD22-A103, +150°C, 1000 hrs	25	0/25	Pass
Bond Pull Strength	M2011	5	0/5	Pass
Bond Shear	JED22-B116	5	0/5	Pass
Moisture Classification	J-STD-020, MSL1	25	0/25, x2 lots	MSL1, 260°C

§ With MSL preconditioning per JESD22-A113, MSL 1 (260C)